

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | | |
|--|-----------|--|--|--|--|
| V _{DS} (V) | 40 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.0017 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$ | 0.0020 | | | | |
| I _D (A) | 200 | | | | |
| Configuration | Single | | | | |
| Package | TO-263-7L | | | | |

FEATURES

• TrenchFET® power MOSFET

N-Channel MOSFET

- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





| ABSOLUTE MAXIMUM RATIN PARAMETER | , | SYMBOL | LIMIT | UNIT | |
|--|--------------------------|-----------------------------------|-------------|------|--|
| Drain-Source Voltage | | V _{DS} | 40 | | |
| Gate-Source Voltage | | V _{GS} | ± 20 | · | |
| Continuous Drain Current | T _C = 25 °C a | I _D | 200 | A | |
| | T _C = 125 °C | | 193 | | |
| Continuous Source Current (Diode Condu | ction) ^a | I _S | 200 | | |
| Pulsed Drain Current ^b | | I _{DM} | 600 | | |
| Single Pulse Avalanche Current | | I _{AS} | 95 | | |
| Single Pulse Avalanche Energy | L = 0.1 mH | E _{AS} | 451 | mJ | |
| Martin as Brown Bloods attach | T _C = 25 °C | D | 375 | W | |
| Maximum Power Dissipation ^b | T _C = 125 °C | P_{D} | 125 | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stq} | -55 to +175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------|------------------------|------------|-------|------|--|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | | |
| Junction-to-Ambient | PCB Mount ^c | R_{thJA} | 40 | °C/W | | |
| Junction-to-Case (Drain) | | R_{thJC} | 0.4 | C/VV | | |

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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| PARAMETER | SYMBOL | TES | MIN. | TYP. | MAX. | UNIT | | |
|---|-------------------------|---|---|------|--------|--------|------|--|
| Static | | | | l | | I. | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | | 40 | - | - | V | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | | 2.0 | 2.5 | V | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | - | ± 100 | nA | |
| | | V _{GS} = 0 V | V _{DS} = 40 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 125 °C | - | - | 50 | μA | |
| | | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 175 °C | - | - | 250 | | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 \text{ V}$ | 200 | - | =. | Α | |
| | | V _{GS} = 10 V | I _D = 30 A | - | 0.0012 | 0.0017 | Ω | |
| Drain-Source On-State Resistance a | В | V _{GS} = 10 V | I _D = 30 A, T _J = 125 °C | - | - | 0.0028 | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V | I _D = 30 A, T _J = 175 °C | - | - | 0.0034 | | |
| | | V _{GS} = 4.5 V | I _D = 20 A | - | 0.0014 | 0.0020 | | |
| Forward Transconductance b | 9fs | V _{DS} = 15 V, I _D = 30 A | | - | 181 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 8934 | 11 168 | pF | |
| Output Capacitance | Coss | $V_{GS} = 0 V$ | $V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$ | - | 1592 | 1990 | | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 928 | 1160 | | |
| Total Gate Charge ^c | Q_g | | | - | 194 | 291 | | |
| Gate-Source Charge ^c | Q_{gs} | V _{GS} = 10 V | $V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}$ | - | 25 | - | nC | |
| Gate-Drain Charge ^c | Q_{gd} | | | - | 40 | - | | |
| Gate Resistance | R_g | f = 1 MHz | | 0.25 | 0.8 | 1.8 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | $V_{DD} = 20 \text{ V, } R_L = 1 \Omega$ $I_D \cong 20 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$ | | - | 22 | 33 | | |
| Rise Time ^c | t _r | | | - | 17 | 26 | - ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 70 | 105 | | |
| Fall Time ^c | t _f | | | - | 16 | 24 | | |
| Source-Drain Diode Ratings and Chara | cteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 600 | Α | |
| Forward Voltage | V_{SD} | I _F = 60 A, V _{GS} = 0 V | | _ | 0.8 | 1.5 | V | |

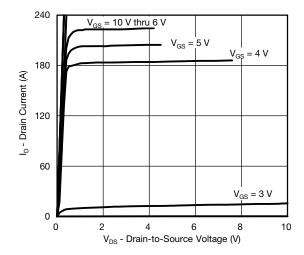
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

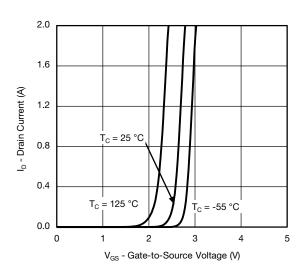
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



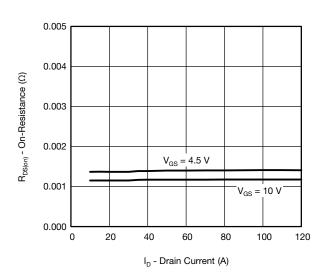
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



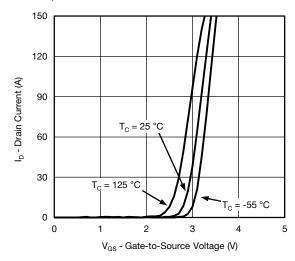
Output Characteristics



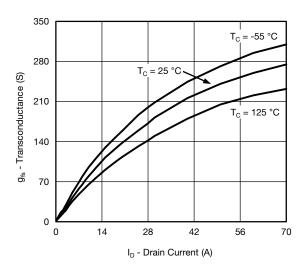
Transfer Characteristics



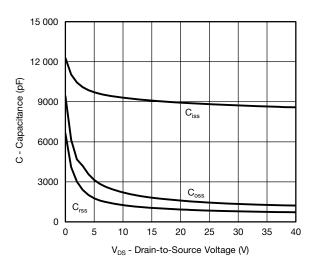
On-Resistance vs. Drain Current



Transfer Characteristics



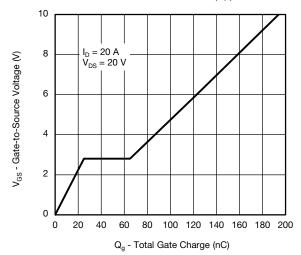
Transconductance



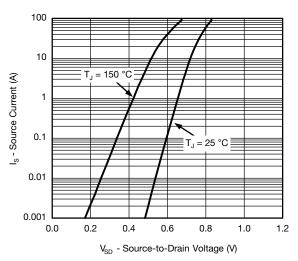
Capacitance



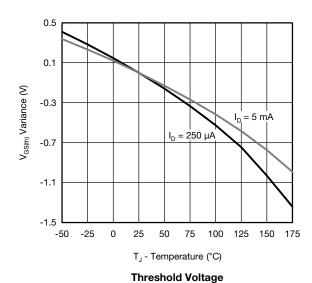
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

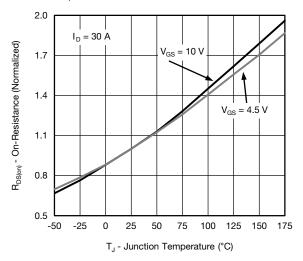


Gate Charge

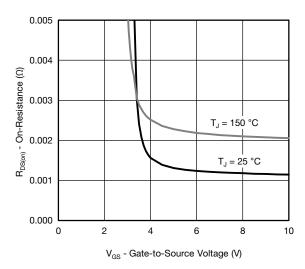


Source Drain Diode Forward Voltage

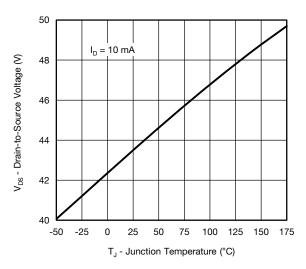




On-Resistance vs. Junction Temperature



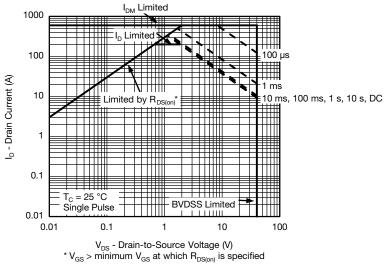
On-Resistance vs. Gate-to-Source Voltage



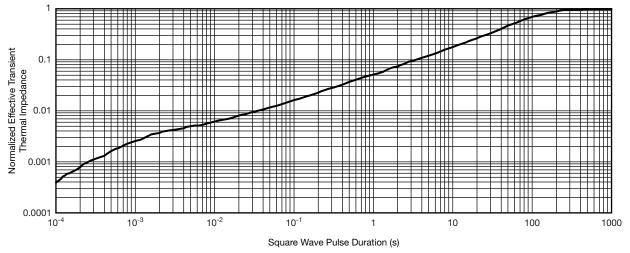
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



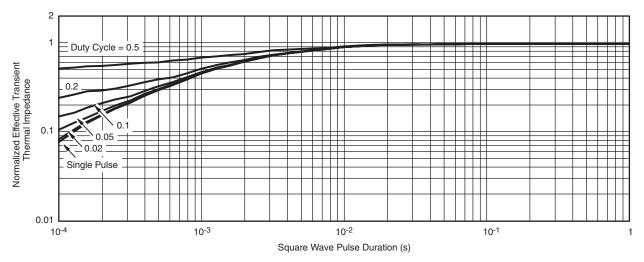
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267058.



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| REVISION HISTORY ^a | | | | |
|-------------------------------|-----------|--------------------------------------|--|--|
| REVISION | DATE | DESCRIPTION OF CHANGE | | |
| В | 04-Aug-15 | Revised R _g minimum limit | | |

Note

a. As of April 2014

Vishay Siliconix

D²PAK / TO-263 and TO-262

Ordering codes for the SQ rugged series power MOSFETs in the D²PAK / TO-263 and TO-262 packages:

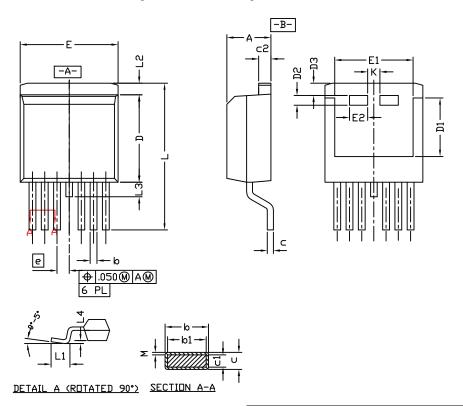
| DATASHEET PART NUMBER | OLD ORDERING CODE a | NEW ORDERING CODE | |
|-----------------------|---------------------|--------------------|--|
| SQM100N04-2m7 | SQM100N04-2M7-GE3 | SQM100N04-2M7_GE3 | |
| SQM100N10-10 | SQM100N10-10-GE3 | SQM100N10-10_GE3 | |
| SQM110N05-06L | SQM110N05-06L-GE3 | SQM110N05-06L_GE3 | |
| SQM110P06-8m9L | SQM110P06-8M9L-GE3 | SQM110P06-8M9L_GE3 | |
| SQM120N02-1m3L | SQM120N02-1M3L-GE3 | SQM120N02-1M3L_GE3 | |
| SQM120N03-1m5L | SQM120N03-1M5L-GE3 | SQM120N03-1M5L_GE3 | |
| SQM120N04-1m7 | SQM120N04-1M7-GE3 | SQM120N04-1M7_GE3 | |
| SQM120N04-1m7L | SQM120N04-1M7L-GE3 | SQM120N04-1M7L_GE3 | |
| SQM120N04-1m9 | SQM120N04-1M9-GE3 | SQM120N04-1M9_GE3 | |
| SQM120N06-06 | SQM120N06-06-GE3 | SQM120N06-06_GE3 | |
| SQM120N06-3m5L | SQM120N06-3M5L-GE3 | SQM120N06-3M5L_GE3 | |
| SQM120N10-09 | SQM120N10-09-GE3 | SQM120N10-09_GE3 | |
| SQM120N10-3m8 | SQM120N10-3M8-GE3 | SQM120N10-3M8_GE3 | |
| SQM120P04-04L | SQM120P04-04L-GE3 | SQM120P04-04L_GE3 | |
| SQM120P06-07L | SQM120P06-07L-GE3 | SQM120P06-07L_GE3 | |
| SQM120P10-10m1L | - | SQM120P10_10m1LGE3 | |
| SQM200N04-1m1L | SQM200N04-1M1L-GE3 | SQM200N04-1M1L_GE3 | |
| SQM200N04-1m7L | SQM200N04-1M7L-GE3 | SQM200N04-1M7L_GE3 | |
| SQM200N04-1m8 | SQM200N04-1M8-GE3 | SQM200N04-1M8_GE3 | |
| SQM25N15-52 | SQM25N15-52-GE3 | SQM25N15-52_GE3 | |
| SQM35N30-97 | SQM35N30-97-GE3 | SQM35N30-97_GE3 | |
| SQM40010EL | - | SQM40010EL_GE3 | |
| SQM40N10-30 | SQM40N10-30-GE3 | SQM40N10-30_GE3 | |
| SQM40N15-38 | SQM40N15-38-GE3 | SQM40N15-38_GE3 | |
| SQM40P10-40L | SQM40P10-40L-GE3 | SQM40P10-40L_GE3 | |
| SQM47N10-24L | SQM47N10-24L-GE3 | SQM47N10-24L_GE3 | |
| SQM50020EL | - | SQM50020EL_GE3 | |
| SQM50N04-4m0L | SQM50N04-4M0L-GE3 | SQM50N04-4M0L_GE3 | |
| SQM50N04-4m1 | SQM50N04-4M1-GE3 | SQM50N04-4M1_GE3 | |
| SQM50P03-07 | SQM50P03-07-GE3 | SQM50P03-07_GE3 | |
| SQM50P04-09L | SQM50P04-09L-GE3 | SQM50P04-09L_GE3 | |
| SQM50P06-15L | SQM50P06-15L-GE3 | SQM50P06-15L_GE3 | |
| SQM50P08-25L | SQM50P08-25L-GE3 | SQM50P08-25L_GE3 | |
| SQM60030E | - | SQM60030E_GE3 | |
| SQM60N06-15 | SQM60N06-15-GE3 | SQM60N06-15_GE3 | |
| SQM60N20-35 | SQM60N20-35-GE3 | SQM60N20-35_GE3 | |
| SQM70060EL | - - | SQM70060EL_GE3 | |
| SQM85N15-19 | SQM85N15-19-GE3 | SQM85N15-19_GE3 | |
| SQV120N10-3m8 | SQV120N10-3m8-GE3 | SQV120N10-3m8 GE3 | |
| SQV120N06-4m7L | 521.221.13 6 525 | SQV120N06-4m7L GE3 | |

Note

a. Old ordering code is obsolete and no longer valid for new orders



D²PAK (TO-263-7L) Case Outline



Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

| | INCHES | | MILLIN | METERS | |
|--|-----------|-------|----------|--------|--|
| DIM. | MIN. | MAX. | MIN. | MAX. | |
| Α | 0.160 | 0.190 | 4.064 | 4.826 | |
| b | 0.020 | 0.039 | 0.508 | 0.990 | |
| b1 | 0.020 | 0.035 | 0.508 | 0.889 | |
| b2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| c* SUB | 0.012 | 0.018 | 0.305 | 0.457 | |
| c* SUM | 0.022 | 0.028 | 0.559 | 0.711 | |
| c1 | 0.018 | 0.025 | 0.457 | 0.635 | |
| c2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| D | 0.340 | 0.380 | 8.636 | 9.652 | |
| D1 | 0.220 | 0.240 | 5.588 | 6.096 | |
| D2 | 0.038 | 0.042 | 0.965 | 1.067 | |
| D3 | 0.045 | 0.055 | 1.143 | 1.397 | |
| Е | 0.380 | 0.410 | 9.652 | 10.414 | |
| E1 | 0.245 | - | 6.223 | - | |
| E2 | 0.072 | 0.078 | 1.829 | 1.981 | |
| е | 0.050 | BSC | 1.27 BSC | | |
| K | 0.045 | 0.055 | 1.143 | 1.397 | |
| L | 0.575 | 0.625 | 14.605 | 15.875 | |
| L1 | 0.090 | 0.110 | 2.286 | 2.794 | |
| L2 | 0.040 | 0.055 | 1.016 | 1.397 | |
| L3 | 0.050 | 0.070 | 1.270 | 1.778 | |
| L4 | 0.010 BSC | | 0.254 | BSC | |
| М | - | 0.002 | - | 0.050 | |
| ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006 | | | | | |

1 Document Number: 63782



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